

EVVOSEMI[®]

THINK CHANGE DO



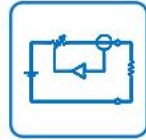
ESD



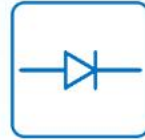
TVS



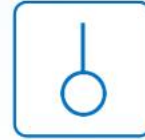
MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	MJ15003
▶ Overseas	Part Number	MJ15003
▶ Equivalent	Part Number	MJ15003

EV is the abbreviation of name EVVO

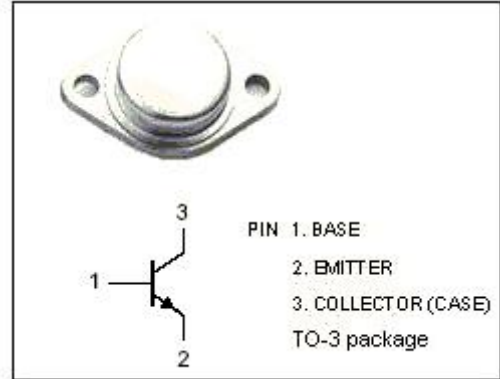
Silicon NPN Power Transistor

DESCRIPTION

- High DC Current Gain-
: $h_{FE} = 25(\text{Min})@I_C = 5A$
- Wide Area of Safe Operation
- Complement to the PNP MJ15004

APPLICATIONS

- Designed for high power audio, disk head positioners and other linear applications.

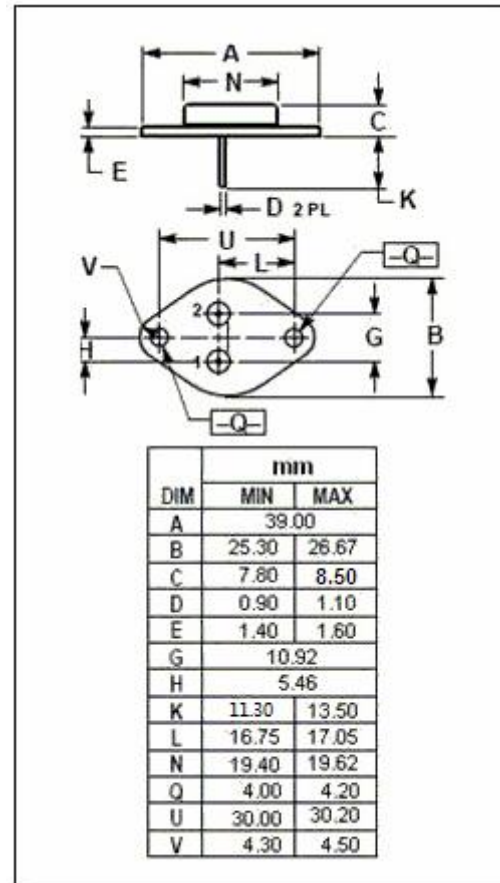


ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	140	V
V_{CEO}	Collector-Emitter Voltage	140	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	20	A
I_B	Base Current-Continuous	5	A
P_D	Total Power Dissipation@ $T_c=25^\circ\text{C}$	250	W
T_j	Junction Temperature	200	$^\circ\text{C}$
T_{stg}	Storage Temperature	-65~200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	0.7	$^\circ\text{C}/\text{W}$



ELECTRICAL CHARACTERISTICS
T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 50mA ; I _B = 0	140		V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 0.5A		1	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 5A ; V _{CE} = 2V		2	V
I _{CEO}	Collector Cutoff Current	V _{CE} = 140V; I _B = 0		0.25	mA
I _{CBO}	Collector Cutoff Current	V _{CB} = 140V; I _E =0 V _{CB} = 140V; I _E =0; T _C = 150°C		0.1 2.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0		0.1	mA
h _{FE}	DC Current Gain	I _C = 5A ; V _{CE} = 2V	25	150	
I _{s/b}	Second Breakdown Collector Current with Base Forward Biased	V _{CE} = 100V, t= 1s, Nonrepetitive	1		A
C _{OB}	Output Capacitance	I _E = 0 ; V _{CB} = 10V; f _{test} = 1.0MHz		1000	pF
f _T	Current-Gain—Bandwidth Product	I _C = 0.5A ; V _{CE} = 10V; f _{test} = 0.5MHz	2		MHz

Disclaimer

EVVOSEMI ("EVVO") reserves the right to make corrections, enhancements, improvements, and other changes to its products and services at any time, and to discontinue any product or service without notice.

EVVO warrants the performance of its hardware products to the specifications applicable at the time of sale in accordance with its standard warranty. Testing and other quality control techniques are used as deemed necessary by EVVO to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

Customers should obtain and confirm the latest product information and specifications before final design, purchase, or use. EVVO makes no warranty, representation, or guarantee regarding the suitability of its products for any particular purpose, nor does EVVO assume any liability for application assistance or customer product design. EVVO does not warrant or accept any liability for products that are purchased or used for any unintended or unauthorized application.

EVVO products are not authorized for use as critical components in life support devices or systems without the express written approval of EVVOSEMI.

The EVVO logo and EVVOSEMI are trademarks of EVVOSEMI or its subsidiaries in relevant jurisdictions. EVVO reserves the right to make changes without further notice to any products herein.